

isc Silicon PNP Power Transistor

2SB920

DESCRIPTION

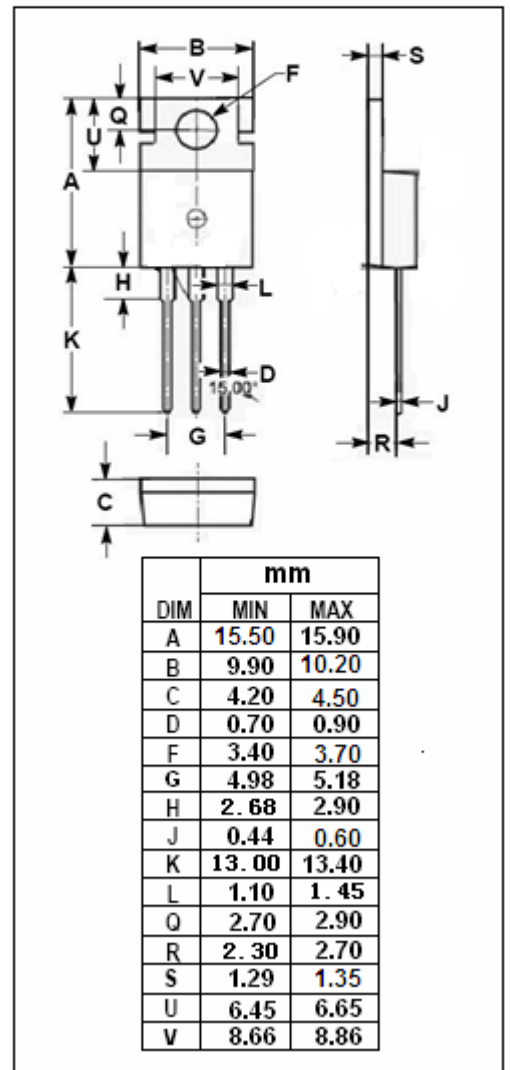
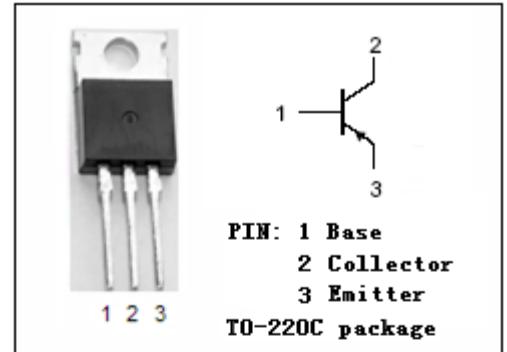
- High Collector Current: $I_C = -5A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.5V(Max) @ I_C = -3A$
- Complement to Type 2SD1236

APPLICATIONS

- Designed for general purpose large current switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-5	A
I_{CM}	Collector Current-Peak	-9	A
P_C	Total Power Dissipation @ $T_C=25^\circ C$	30	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon PNP Power Transistor**2SB920****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; R _{BE} = ∞	-80			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA; I _E = 0	-120			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -3A; I _B = -0.3A			-0.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0			-0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-0.1	mA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -2V	70		280	
h _{FE-2}	DC Current Gain	I _C = -3A; V _{CE} = -2V	30			
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -5V		20		MHz

◆ **h_{FE-1} Classifications**

Q	R	S
70-140	100-200	140-280